



# ElectroMagnetic Analysis and Fault Injection onto Secure Circuits

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# Outline

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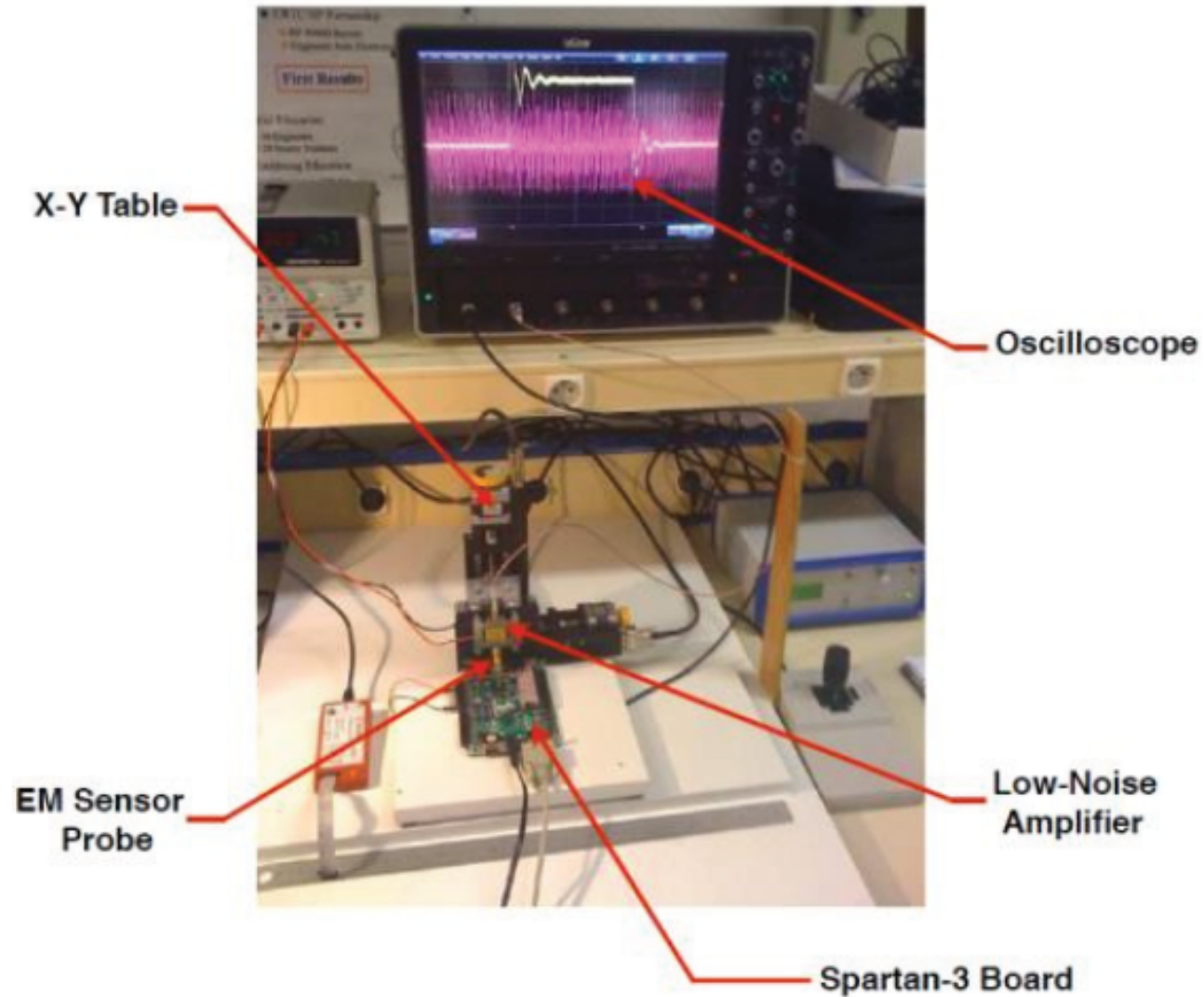
- Context
- Side Channel Analysis
- Fault Injection
- Advanced discussion
- Conclusion/Perspectives

# Context

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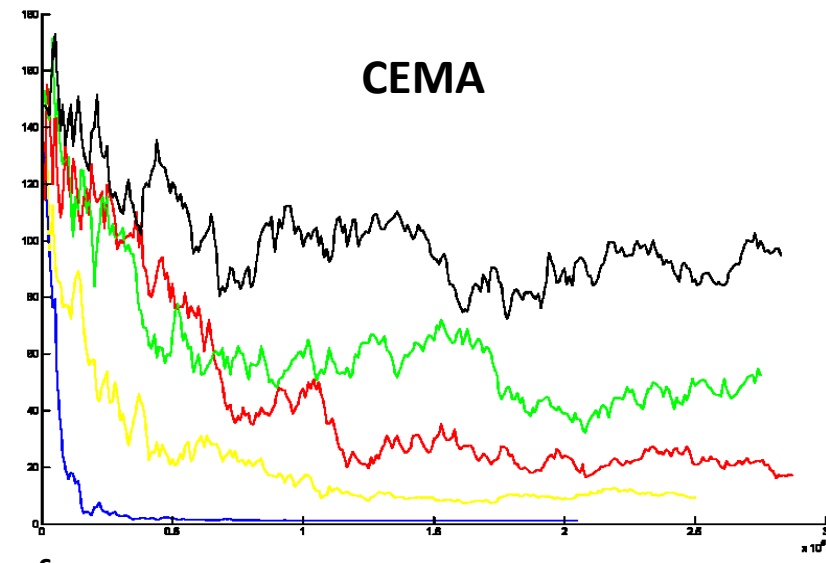
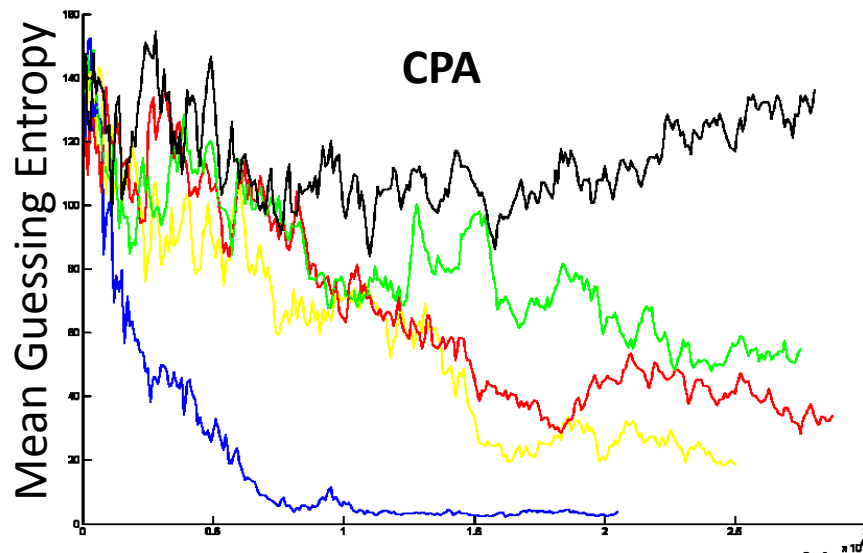
- Implementation attacks are a serious threat to secure designs
  - Side channel analysis, Fault injection, ...
- EM is
  - A very rich information source in passive analysis
    - Power is global, EM is local
  - A versatile medium for active attacks
    - Laser requiring decapsulation and lapping
- Know-How has been largely developed only in recent years

# Analysis Platform



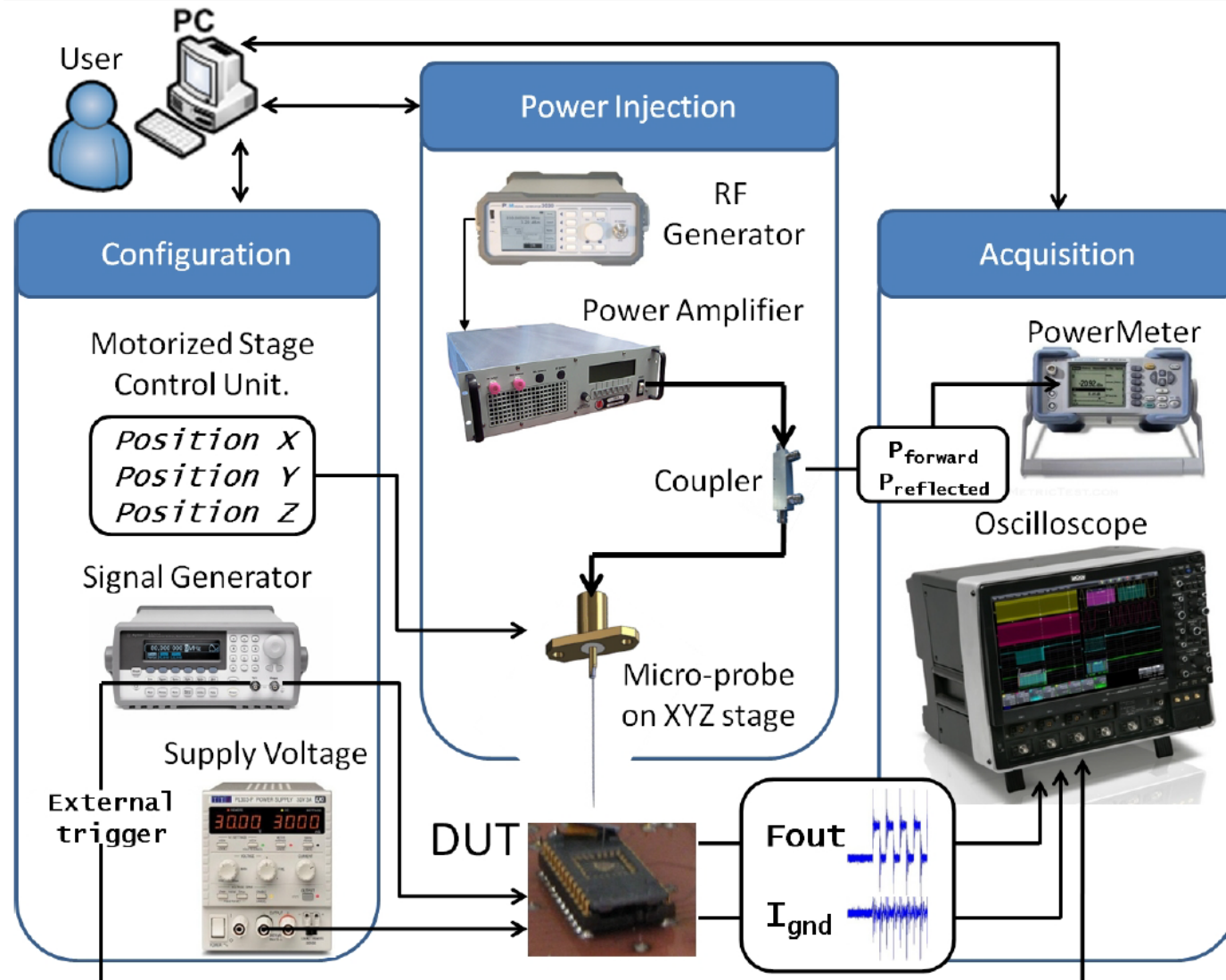
# EM Side Channel Analysis

Design	Power Analysis			EM Analysis		
	Key bytes found	Mean Guessing Entropy	# traces (x10 <sup>3</sup> )	Key bytes found	Mean Guessing Entropy	# traces (x10 <sup>3</sup> )
Unprotected	15	1	205	16	1	155
+ Linear Masking	4	54	275	8	52	275
+ Dynamic Map	5	34	287	9	17	287
+ Dynamic Reloc	7	19	250	12	9	250
+ All	0	136	283	0	94	283



Number of traces

# Injection Platform



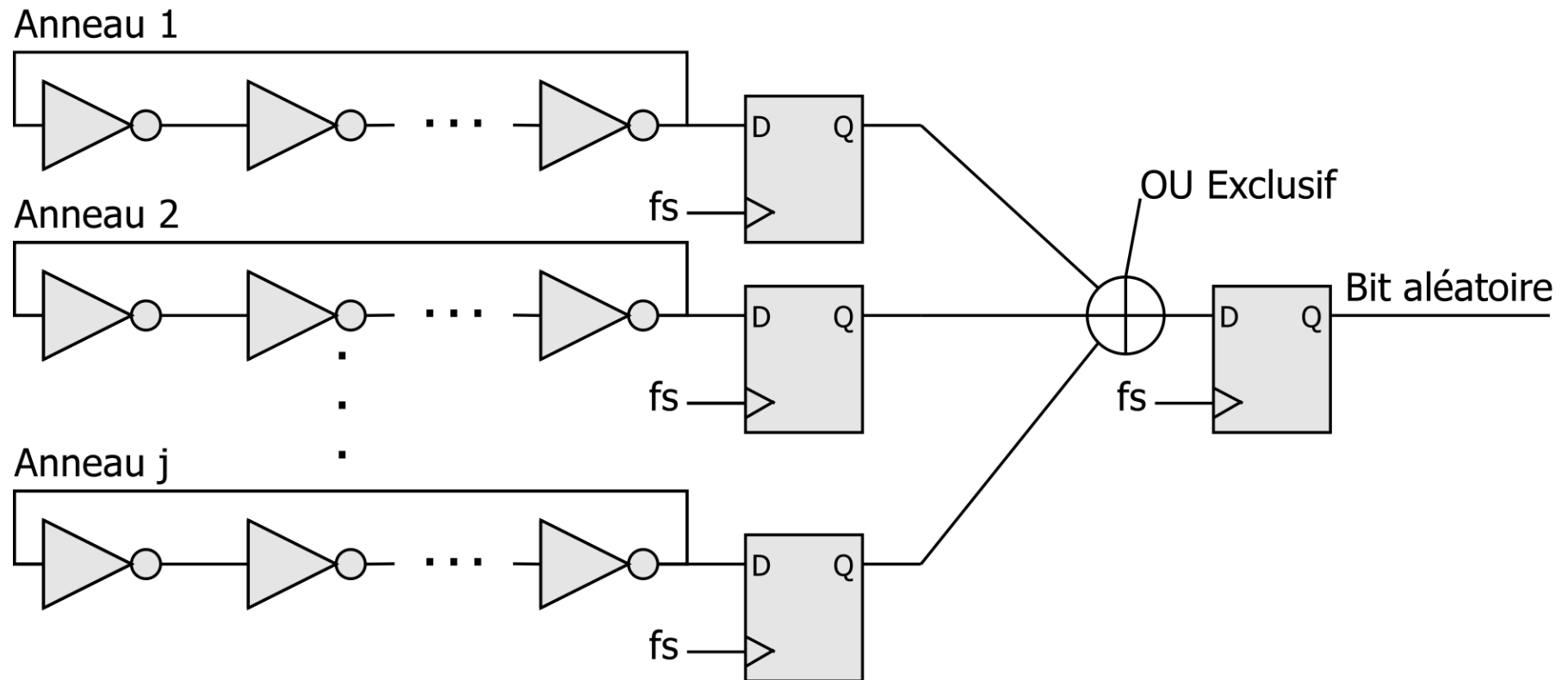
# Fault Injection Results

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- Ring Oscillators
- Random Number Generators
- Cryptographic Coprocessors
- General purpose CPUs

# Target: Ring Oscillators based TRNG

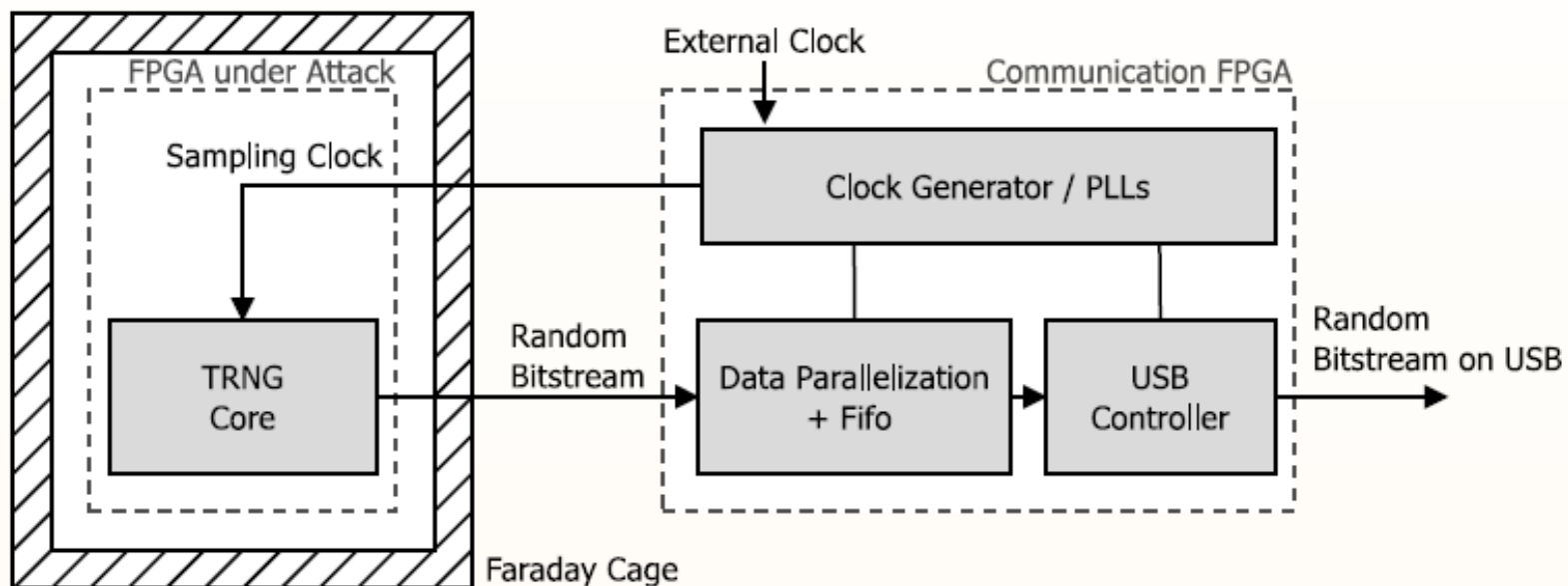
- Use the Ro-generated clock jitter as a source of randomness
- ROs should be independent





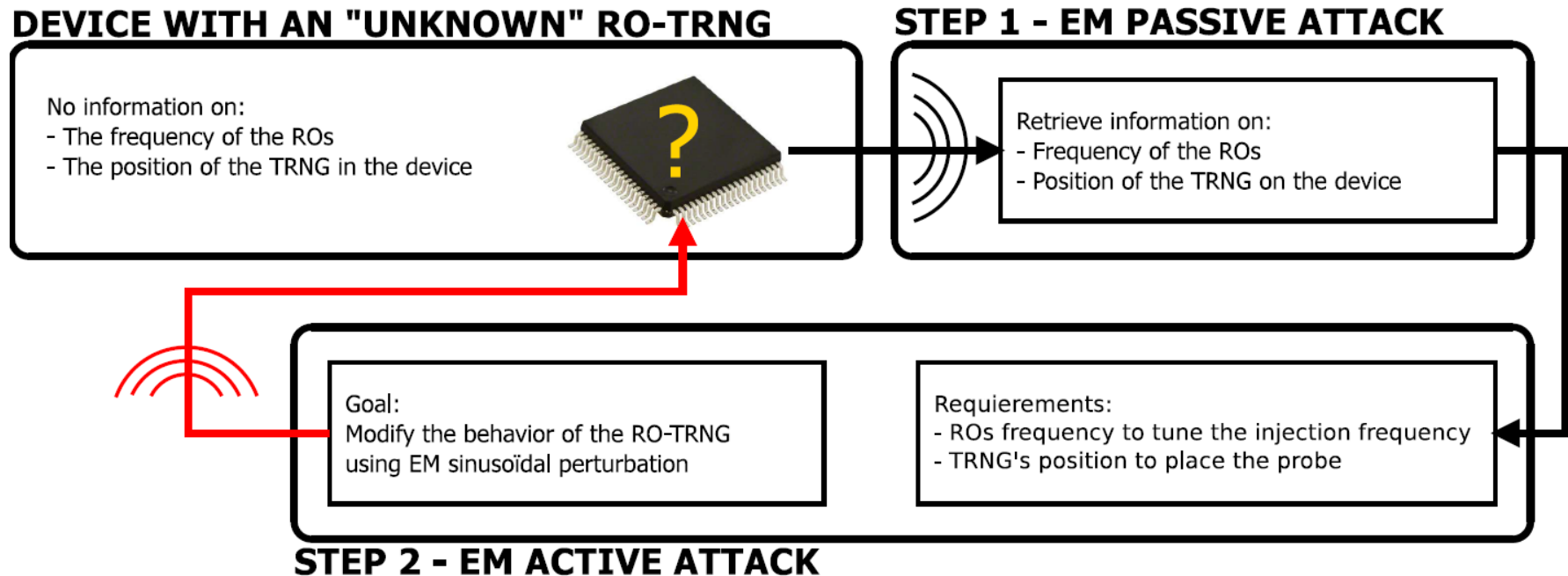
# Design architecture

- The TRNG core is a 50 ROs Wold TRNG
- Working frequencies of the ROs are around 320 MHz
- Sampling frequency: 24 KHz

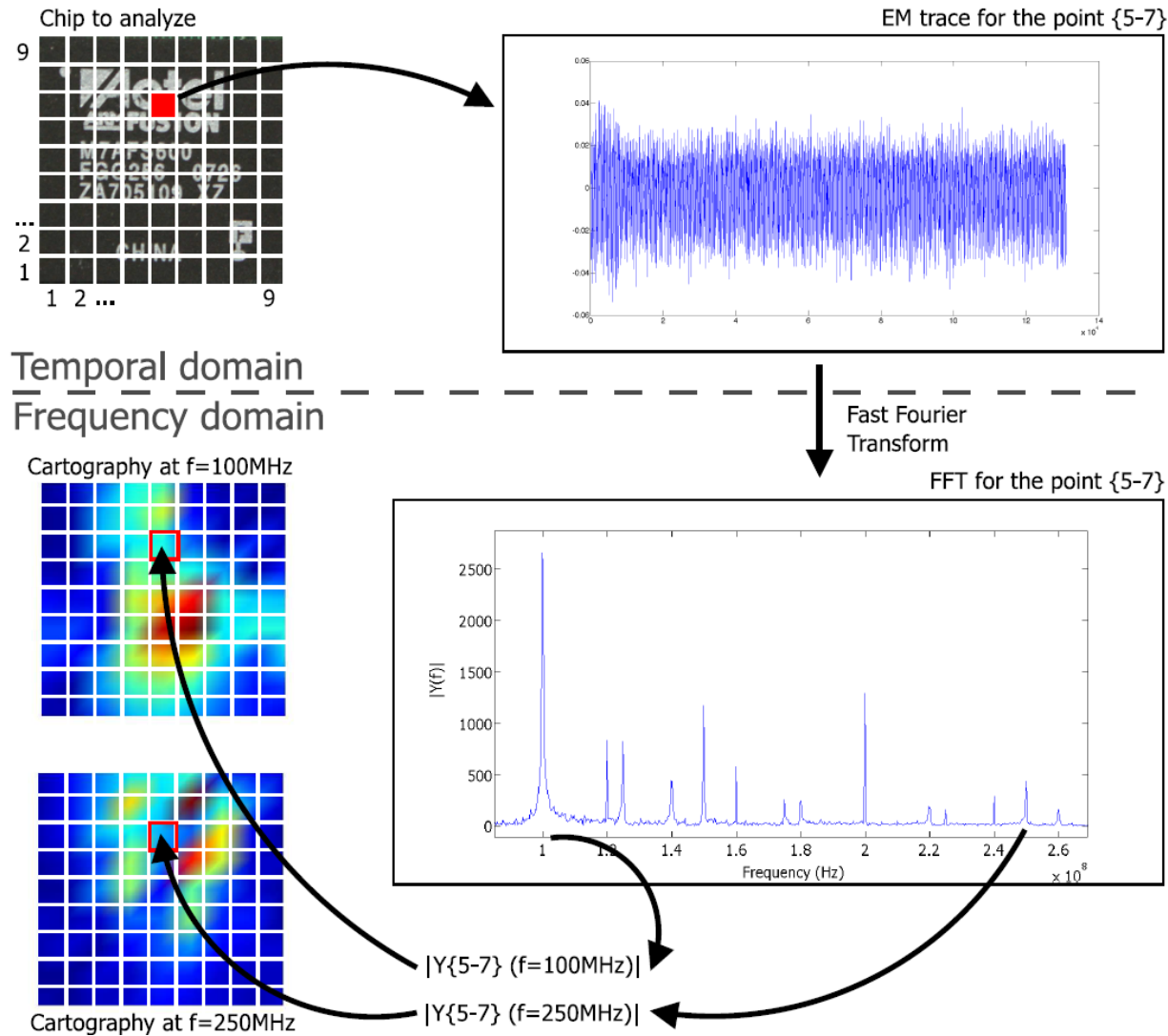


# Attack scenario

- Complementary passive and active EM attacks



# Passive attack: EM cartography



# Active attack: EM harmonic injection

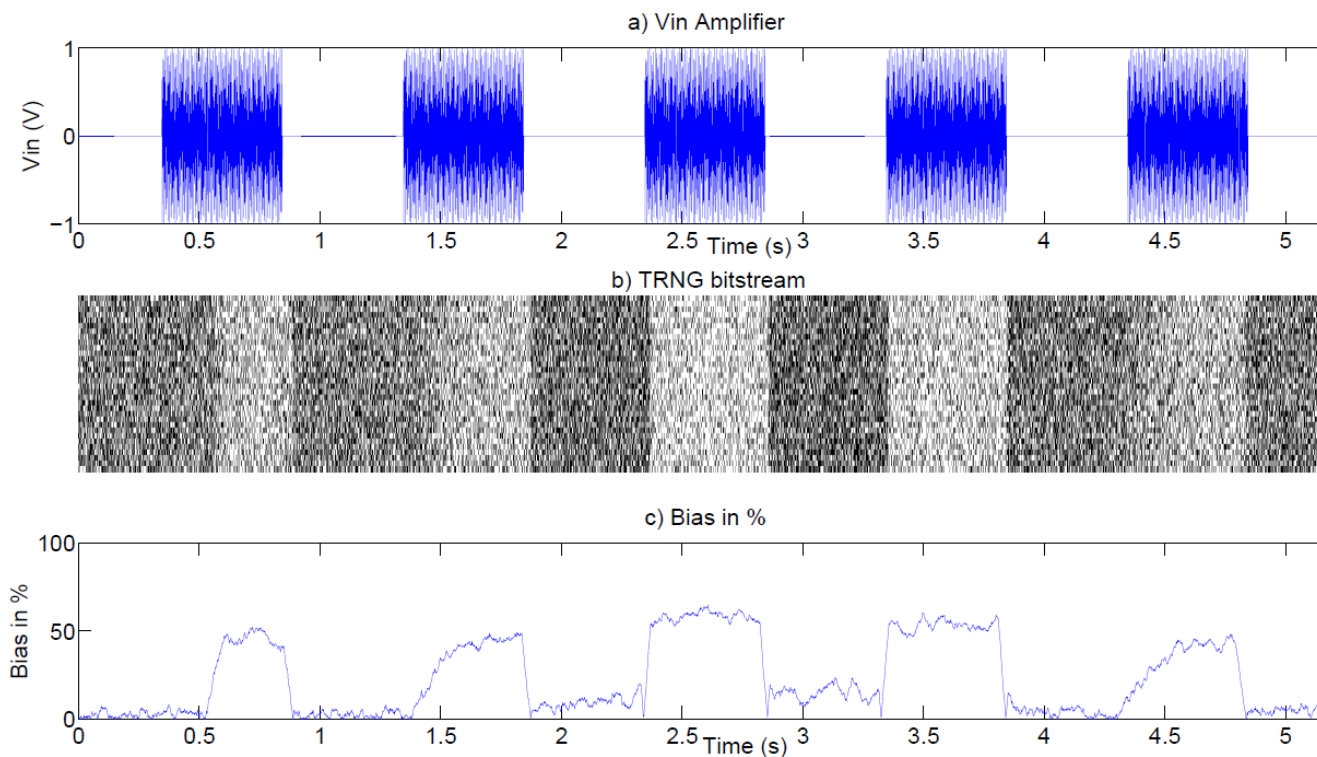
a) No injection   b) PForward 210  $\mu$ W   c) PForward 260  $\mu$ W   d) PForward 300 $\mu$ W



PForward	No Injection	210 $\mu$ W	260 $\mu$ W	300 $\mu$ W
Bias%	0.1%	15.87%	51.57%	55%
NIST tests	SUCCESS	FAIL	FAIL	FAIL

# Dynamic behavior in case of active attack

- The attacks is effective only during the period of the attack.
- The setup and falling time of the attack is directly proportional to the performance of the EM bench



# Fault Injection Results

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- Random Number Generators
- **Cryptographic Coprocessors**
- General purpose CPUs

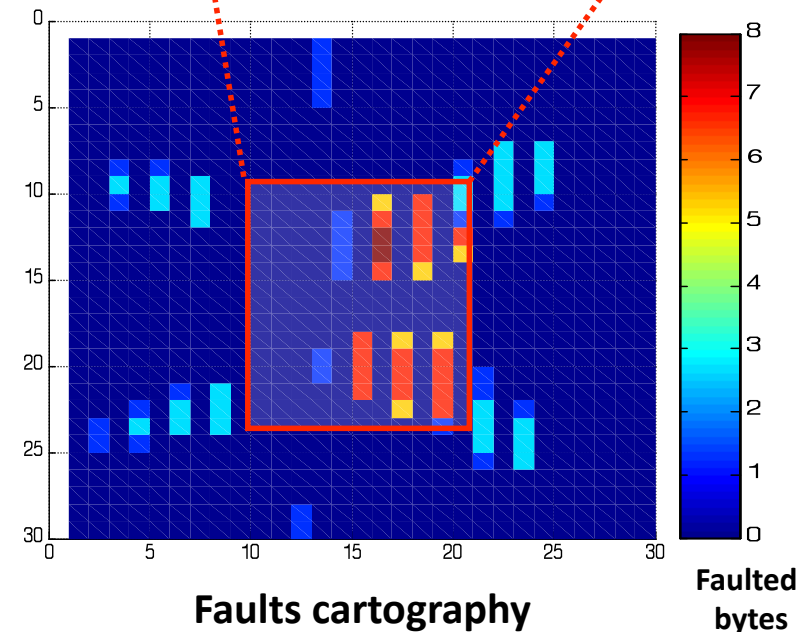
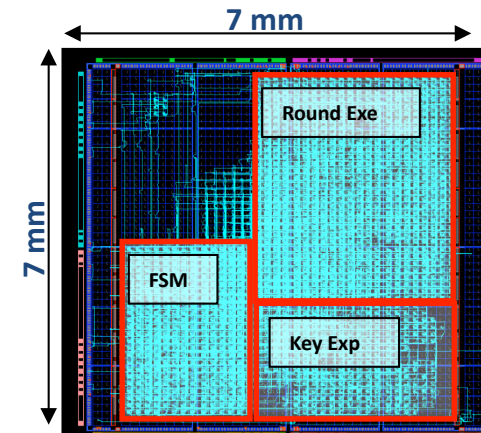
# Crypto-Coprocessors

- FPGA Spartan 3 (130nm)
- Iterative **Hardware AES** implementation
- **100 MHz @ 1.2 volts**
- At each position, an **EMP** is injected **100V-10ns**
- The corresponding faulted ciphertext is retrieved
- **1,000 encryptions** of the same plaintext
- 30x30 different locations
- Antenna **diameter** : **500 μm**
- Displacement **step** : **500 μm**

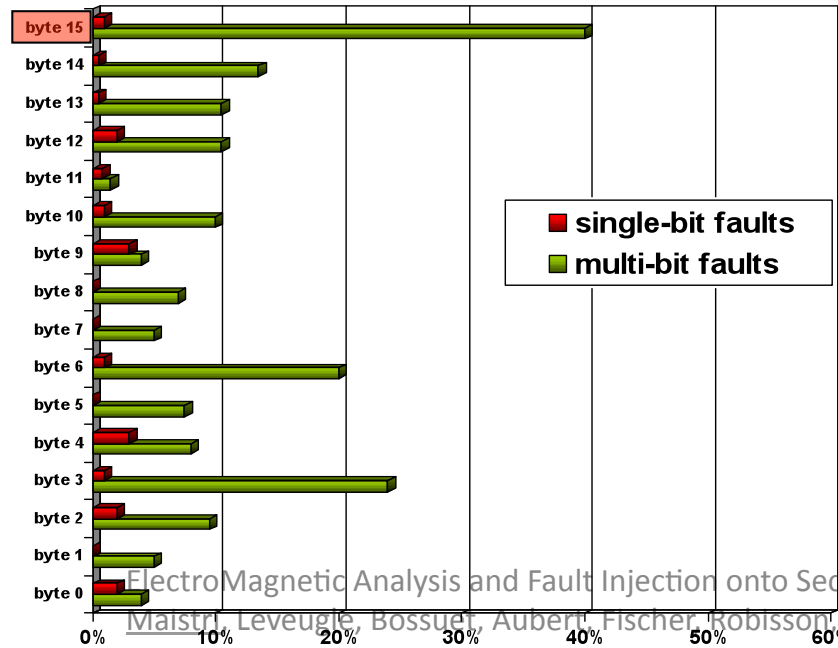
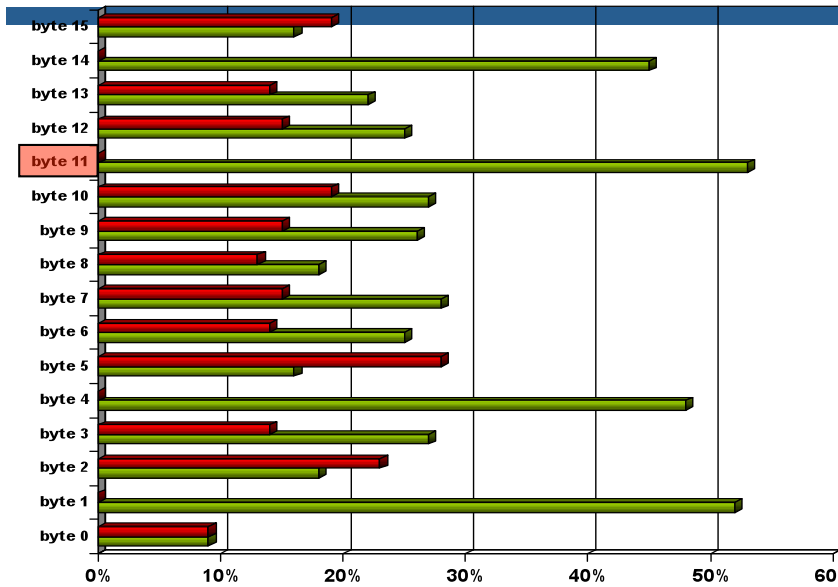
EMP parameters

Z position	EMP amplitude	EMP width	Clk period	Rise/fall times
< 500 μm	100V	10ns	10ns	5ns

- Localized effect of the **EMP**
- Good correlation between the Floorplan and the cartography
- Deterministic and **reproducible effect**

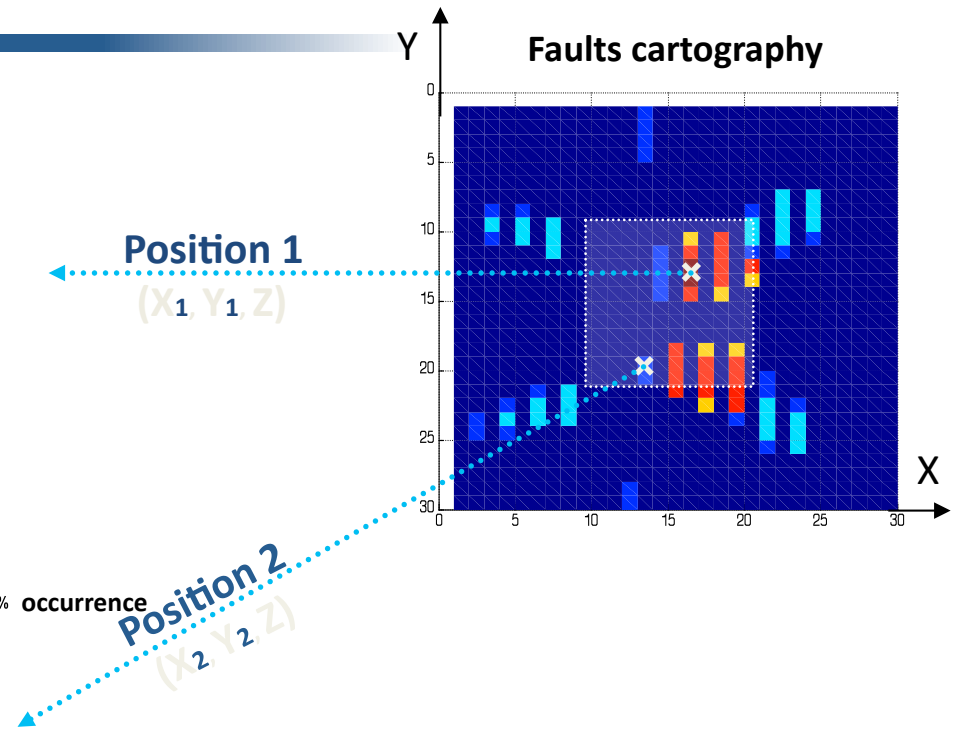


# Crypto-Coprocessors



■ single-bit faults  
■ multi-bit faults

Faults cartography



- Ability to inject **single-bit** and **multi-bits** faults into AES calculations
- Induced faults are **timing faults** (see later)
- May fault any paths (even **subcritical** paths)



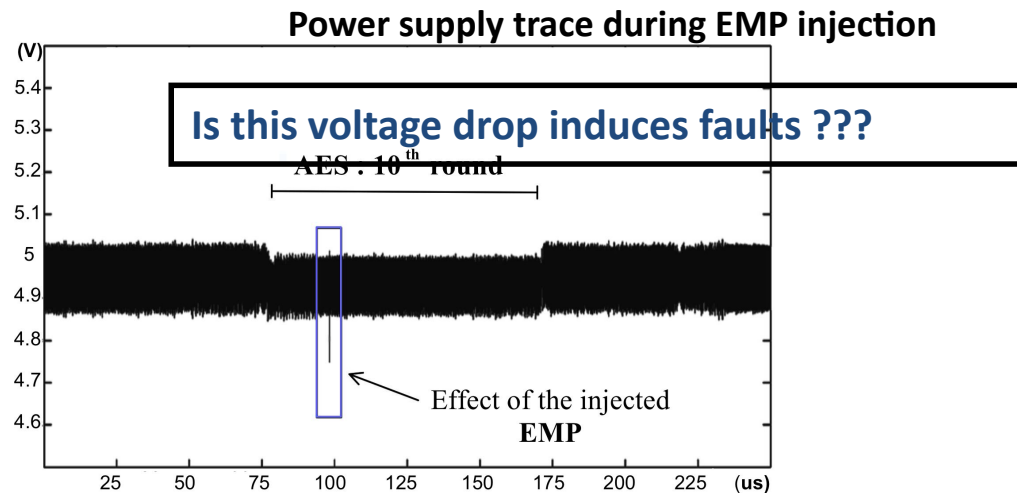
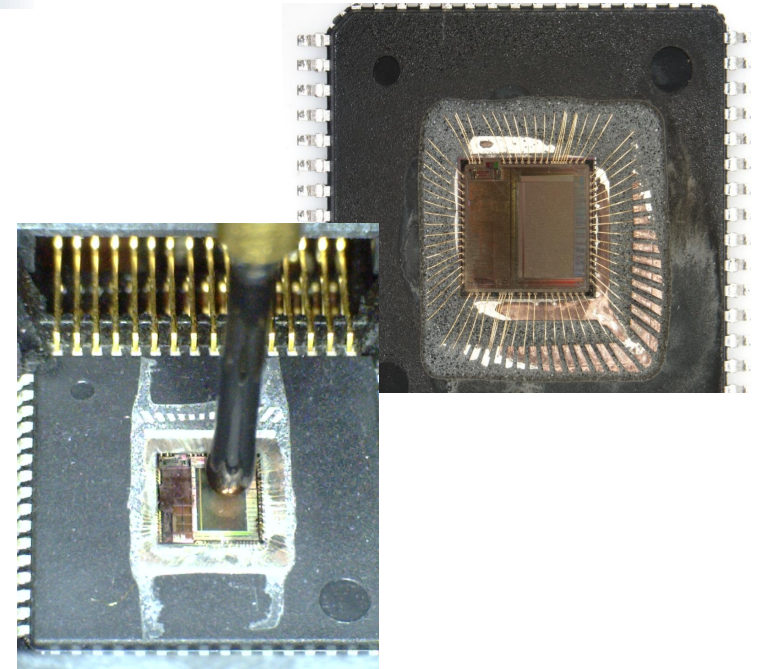
# Fault Injection Results

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- Ring Oscillators
- Random Number Generators
- Cryptographic Coprocessors
- **General purpose CPUs**

# General Purpose CPU (1/2)

- Smartcard emulation board
- 8-bits AVR Atmega 128 MCU (techno **0,35μm**)
- Harvard architecture
- 128 KB Flash program memory
- 4 KB SRAM
- Operating voltage : **4.5 – 5.5 V**
- Operating frequency : **3.57 MHz => Tclk = 280 ns**
- **Software AES implementation**



**EMP parameters**

Z position	EMP amplitude	EMP width	Clk period	Rise/fall times
< 500 μm	100V	50ns	280ns	5ns

**Voltage drop of about 200 mV**

# General Purpose CPU (2/2)

Faulted byte #	Injection time
0	$0.3\mu s$
1	$9.78\mu s$
2	$19.3\mu s$
3	$33.7\mu s$
4	$55.7\mu s$
5	$12.4\mu s$
6	$63.4\mu s$

- Deterministic and **reproducible effect**
- **EMP injection prevents the CPU from executing some instructions by violating the timing constraints**

15	$87.5\mu s$
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# Advanced Modeling

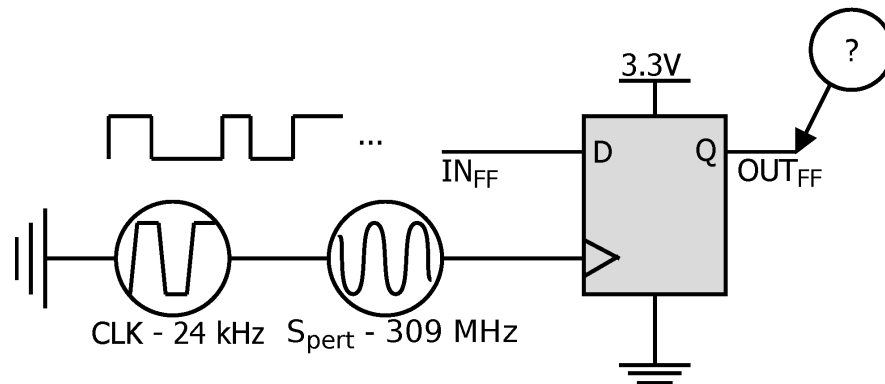
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- Harmonic injections
- Pulsed injections
- Power coupling

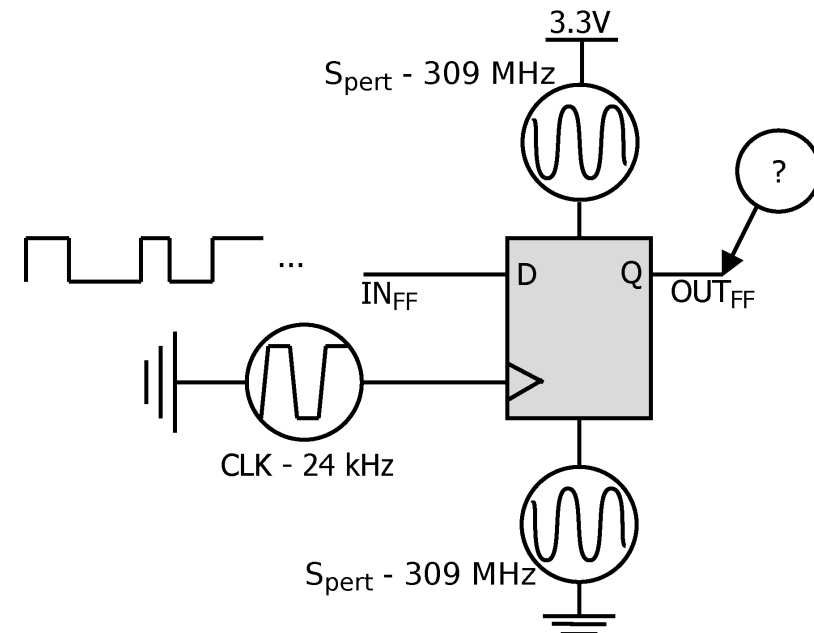
# Harmonic injections

- Faults on DFF used for RO sampling
  - Erroneous sample on (some) clock falling edges
  - Some values not correctly sampled on rising edge (rarer)
- Two possible models describing the behavior:

## Model for Electric field



## Model for Magnetic field



# Advanced Modeling

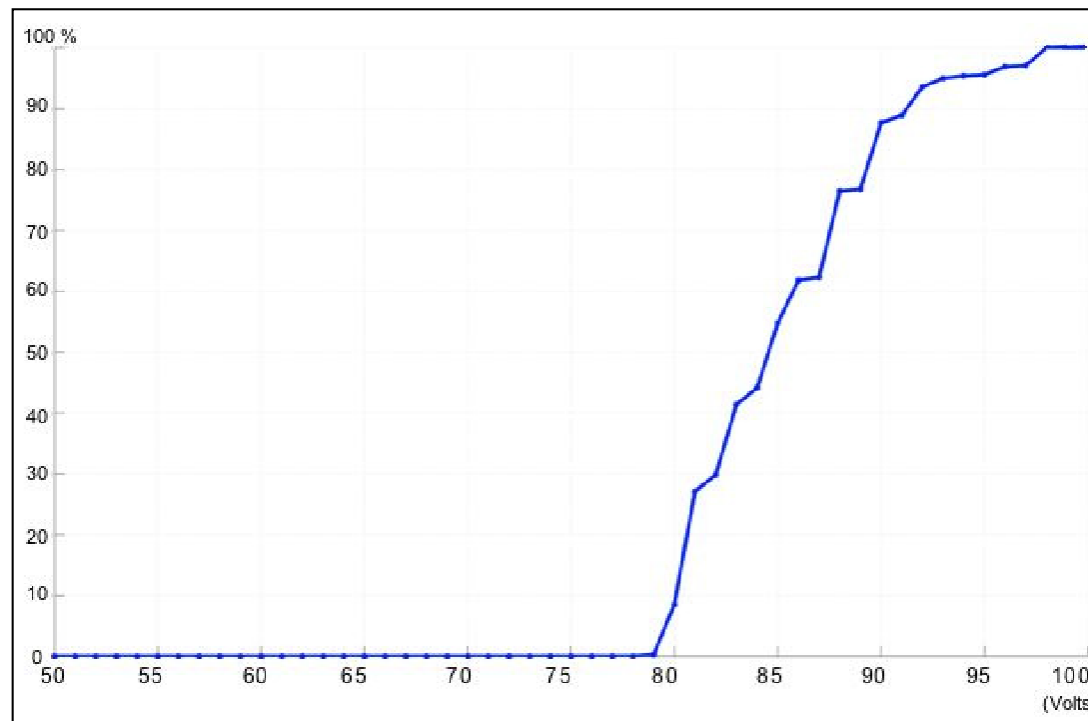
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- Harmonic injections
- Pulsed injections
- Power coupling

# Pulsed injections

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- Strong resemblance to errors from delay faults
  - Increased injected power => Increased error probability
  - Precise clock glitches => very similar error patterns



# Pulsed injections

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- Strong resemblance to errors from delay faults
  - Increased injected power => Increased error probability
  - Precise clock glitches => very similar error patterns
- Interaction EM pulse <> power-ground network
  - Additional delivered energy alters the differential voltage supply
  - Logic under the EM pulsed injection is subject to a lower tension
  - Signal transitions are slower
  - Slowdown larger than available slack → Timing violation
- EM pulsed injections vs Clock/Voltage perturbations:
  - EM local delay fault → Specific locations can be targeted



# Advanced Modeling

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- Harmonic injections
- Pulsed injections
- **Power coupling**

# Power Coupling

	EM Pulse	IR-drop
Spatial connotation	Local	Local
Temporal connotation	Transient	Transient/Dynamic
Effect	Voltage drop	Voltage drop
Source	External	Internal
Origin	Fault injection	Data-dependent computation

- Use IR-drop analysis to
  - Predict most vulnerable regions of the circuit
  - Simulate EM pulses (What-If analysis)
  - Correlate EM/IR-drop cartographies

# Conclusion

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- We demonstrate that it is possible to dynamically control the bias of a RO-TRNG embedded in an FPGA
- The effectiveness of our proposed coupled attack questions the use of ring oscillators in the design of TRNGs

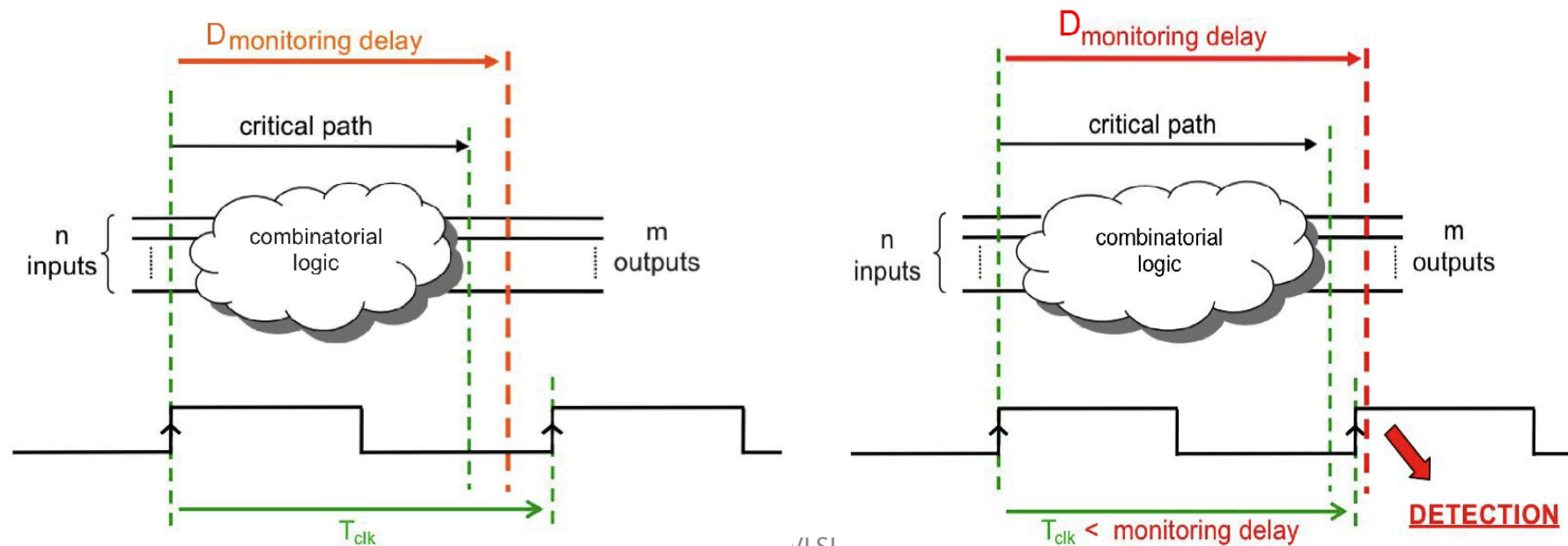
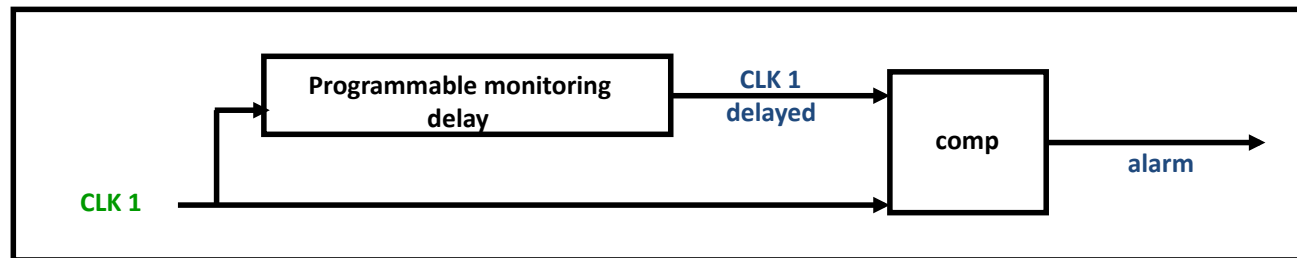
# Q & A

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# BACKUP SLIDES

# Hardware Countermeasure (1/2)

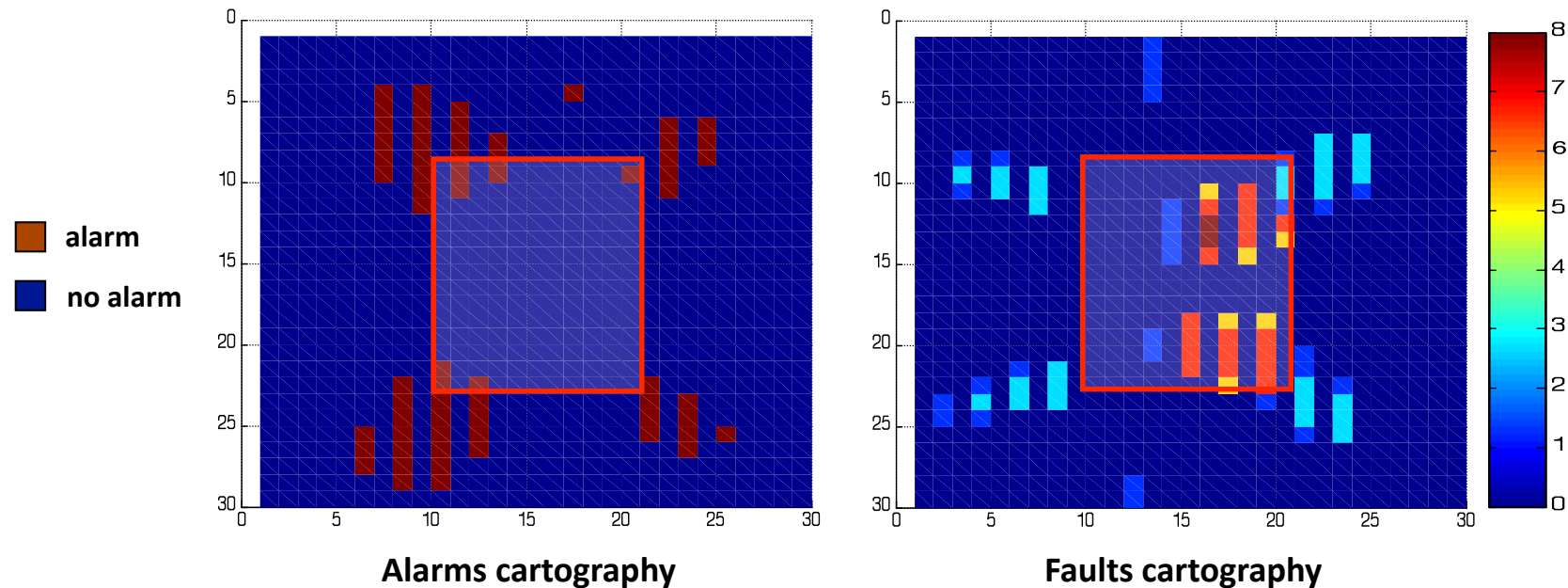


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VLSI

# Hardware Countermeasure (2/2)

- At each position, an **EMP** is injected
- **1,000 encryptions** of the same plaintext
- **30x30 different locations** of the injection probe (step 500  $\mu\text{m}$ )



- Localized effect of the **EMP**
- The EMP is detected only in some positions
- Possibility to induce faults without triggering the alarm